L Number	Hits	Search Text	DB	Time stamp
-	647	(257/288).ccls. and @ad<=20000719	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 12:53
-	77	((257/288).ccls. and @ad<=20000719) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 13:36
-	1	(((257/288).ccls. and @ad<=20000719) and silicide) and 'trench transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 13:36
-	256	@ad<=20000719 and 'silicide' and 'gate' with 'spacer' with 'trench'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:33
-	2	("6201278").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/21 13:53
-	54	(438/259).ccls. and @ad<=20000719 and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:42
-	409	@ad<=20000719 and 'miniaturize' with 'transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:22
-	574	@ad<=20000719 and 'miniaturize' with 'transistor' or 'semiconductor' and 'raised source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:26
-	0	@ad<=20000719 and 'invert sidewall' and 'raised source/drain' and 'STI'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:30
-	6	@ad<=20000719 and 'inverted' with 'spacers' and 'raised source/drain' and 'STI'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:33
-	3	@ad<=20000719 and 'silicide' and 'gate' with 'spacer' with 'trench' and 'STI' and 'raised source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/22 09:34
-	135	(438/270).ccls. and @ad<=20000719 and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36
-	94	(257/330).ccls. and @ad<=20000719 and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36

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-	6	@ad<=20000719 and 'doped channel' and 'raised source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:29
-	966	@ad<=20000719 and (257/330-333).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:37
-	28	(@ad<=20000719 and (257/330-333).ccls.) and 'doped channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:19
-	139	(438/270).ccls. and @ad<=20000719 and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:51
-	97	(257/330).ccls. and @ad<=20000719 and 'silicide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:36
-	984	@ad<=20000719 and (257/408).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:38
-	3231	@ad<=20000719 and (438/300-305).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	84	@ad<=20000719 and (438/242).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:39
-	187	@ad<=20000719 and (438/259).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 15:36
-	73	@ad<=20000719 and (438/376).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:57
-	1	((438/270).ccls. and @ad<=20000719 and 'silicide') and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:51
-	0	((257/330).ccls. and @ad<=20000719 and 'silicide') and 'elevated source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:52
-	202	@ad<=20000719 and 'elevated source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:09
-	2	"20020072184"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:02

-			4	@ad<=20000719 and 'elevated source/drain' and inverted adj1 'spacer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:13
-			2	("5434093").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:12
-			9	@ad<=20000719 and 'raised source/drain' and inverted adj1 spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:39
-			2	"20020072184"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 12:54
-			6	@ad<=20000719 and 'doped channel' and 'raised source/drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:29
-			6	@ad<=20000719 and 'doped channel' and 'raised source drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:30
-			11	@ad<=20000719 and 'IGFET' with 'doped channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:36
-			0	@ad<=20000719 and 'silicide gate' with 'doped channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:36
-			13	@ad<=20000719 and 'silicide gate' and 'doped channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:38
-			2	("6197668").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:38
-			3	@ad<=20000719 and gardner-mark.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:41
-			3	gardner-mark.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:40
-			0	@ad<=20000719 and Mark-Gardner.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:42
-			525	@ad<=20000719 and Gardner-Mark-I.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:10

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-	52	@ad<=20000719 and Gardner-Mark-I.in. and 'punch'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 13:52
-	108	@ad<=20000719 and trench adj1 gate and 'punch'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:11
-	28	(@ad<=20000719 and (257/330-333).ccls.) and 'doped channel'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:24
-	993	(@ad<=20000719 and (257/330-333).ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 14:33
-	145	(@ad<=20000719 and (257/334).ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 15:03
-	9	(("6413823") or ("6406957") or ("6025232") or ("6472260")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 15:04
-	1688	@ad<=20000719 and (438/270-271).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/04 15:38

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